

isc Silicon NPN Darlington Power Transistor

2SD1599

DESCRIPTION

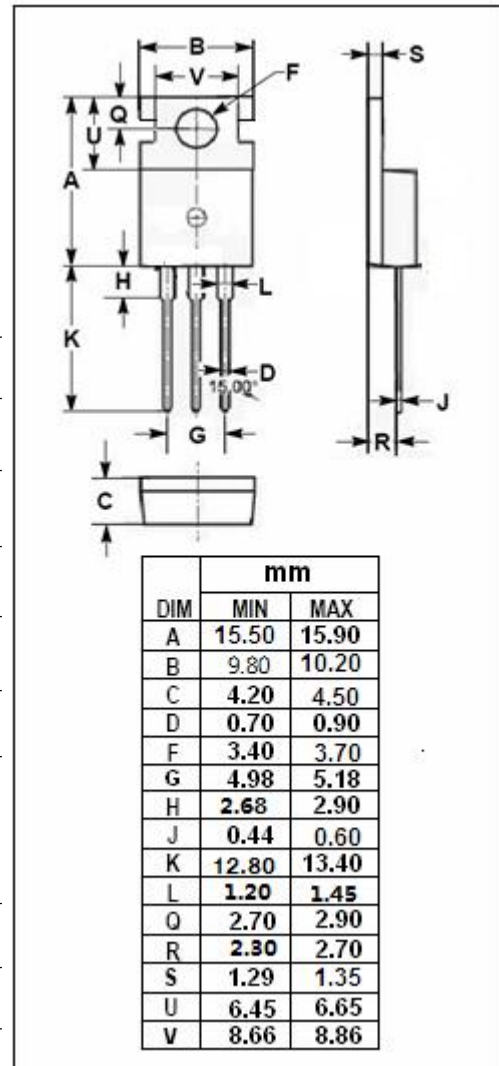
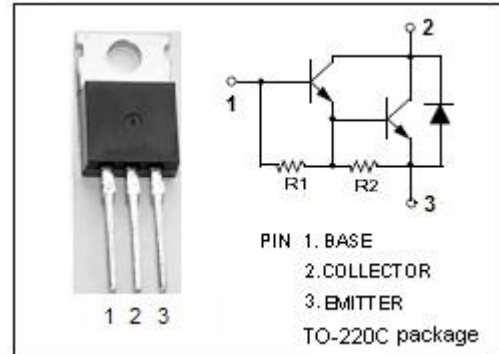
- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ I_C = 2A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = 80V(\text{Min})$
- Low Collector-Emitter Saturation Voltage-
: $V_{CE(\text{sat})} = 2.0V(\text{Max}) @ I_C = 3A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for general purpose amplifier and low speed switching applications

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 80 | V |
| V_{CEO} | Collector-Emitter Voltage | 80 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current-Continuous | 4 | A |
| I_{CM} | Collector Current-Peak | 8 | A |
| P_C | Collector Power Dissipation $T_c = 25^\circ\text{C}$ | 40 | W |
| | Collector Power Dissipation $T_a = 25^\circ\text{C}$ | 2 | |
| T_j | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -65~150 | $^\circ\text{C}$ |



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ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|--|------|------|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _c = 30mA, I _B = 0 | 80 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _c = 3A, I _B = 12mA | | | 2.0 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _c = 3.0A ; V _{CE} = 3V | | | 2.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 80V, I _E = 0 | | | 0.1 | mA |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 80V, I _B = 0 | | | 0.1 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _c = 0 | | | 2 | mA |
| h _{FE-1} | DC Current Gain | I _c = 0.5A ; V _{CE} = 3V | 1000 | | | |
| h _{FE-2} | DC Current Gain | I _c = 2A ; V _{CE} = 3V | 1000 | | | |

Switching times

| | | | | | | |
|------------------|--------------|--|--|-----|--|-----|
| t _{on} | Turn-on Time | I _c =3A; I _{B1} = I _{B2} = 12mA | | 0.5 | | μ s |
| t _{stg} | Storage Time | | | 6.0 | | μ s |
| t _f | Fall Time | | | 1.0 | | μ s |

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